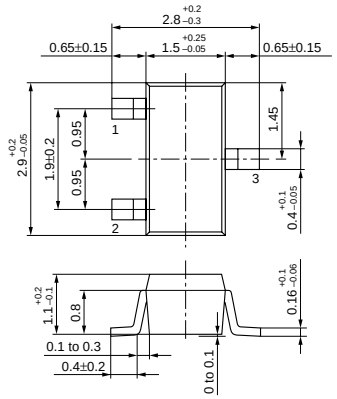
2SC2480

Silicon NPN epitaxial planer type

For high-frequency amplification/oscillation/mixing

Unit: mm



1:Base
2:Emitter
3:Collector

JEDEC:TO–236
EIAJ:SC–59
Mini Type Package

Marking symbol : R

Features

- High transition frequency f_T.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25˚C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

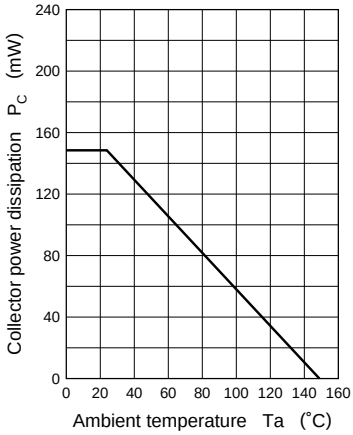
Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	I_C = 100μA, I_E = 0	30			V
Emitter to base voltage	V_{EBO}	I_E = 10μA, I_C = 0	3			V
Forward current transfer ratio	h_{FE}	V_{CB} = 10V, I_E = –2mA	25		250	
Transition frequency	f_T*	V_{CB} = 10V, I_E = –15mA, f = 200MHz	800	1300	1600	MHz
Base to emitter voltage	V_{BE}	V_{CB} = 10V, I_E = –2mA		0.72		V
Common emitter reverse transfer capacitance	C_{re}	V_{CE} = 10V, I_C = 1mA, f = 10.7MHz		1	1.5	pF
Power gain	PG	V_{CB} = 10V, I_E = –1mA, f = 200MHz		20		dB

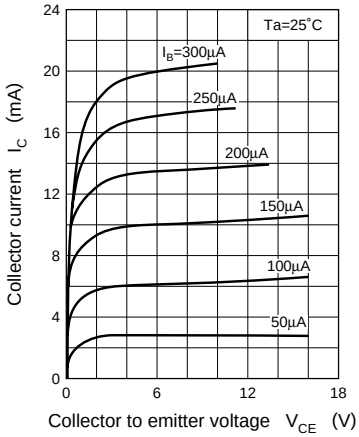
*f_T Rank classification

Rank	T	S
f_T(MHz)	800 ~ 1400	1000 ~ 1600
Marking Symbol	RT	RS

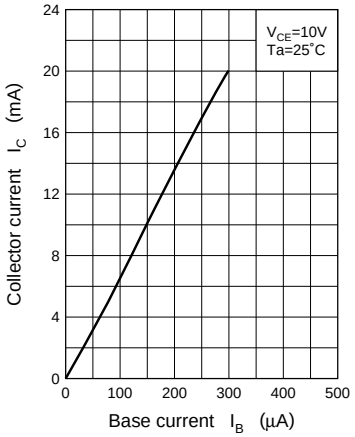
P_C — Ta



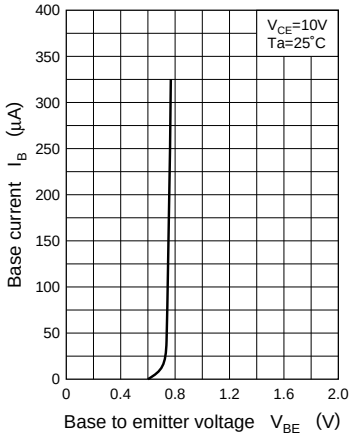
I_C — V_{CE}



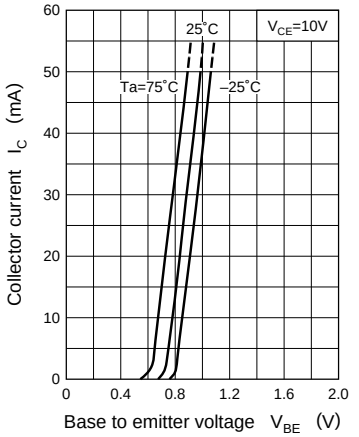
I_C — I_B



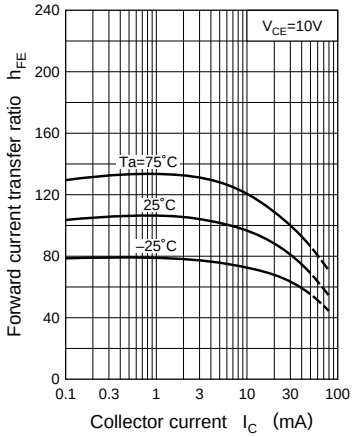
I_B — V_{BE}



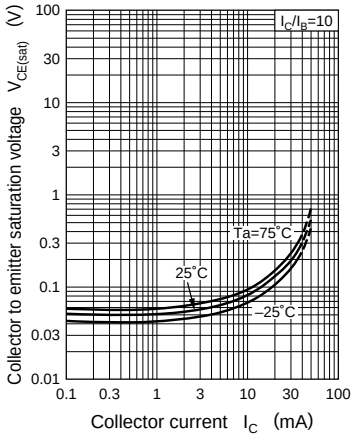
I_C — V_{BE}



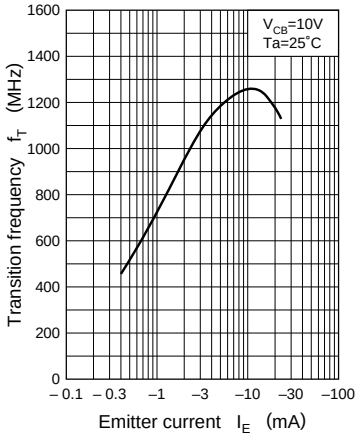
h_{FE} — I_C



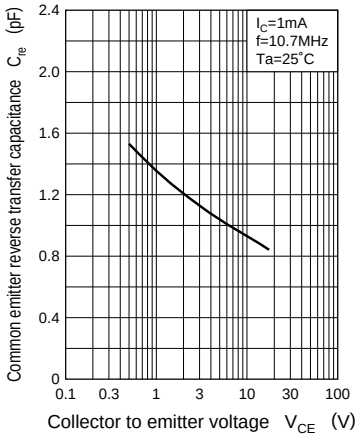
$V_{CE(sat)}$ — I_C



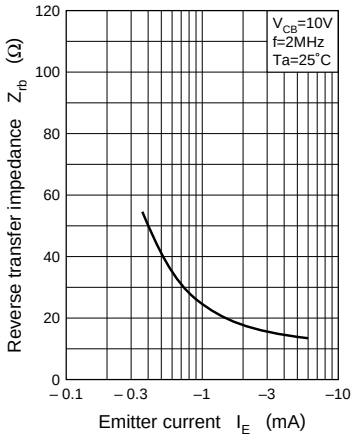
f_T — I_E



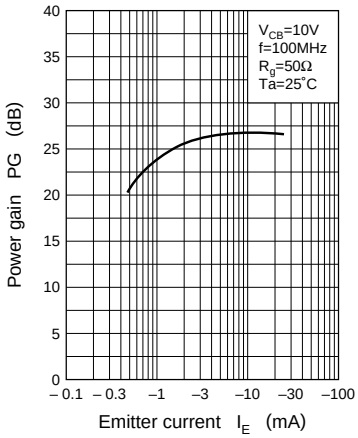
C_{re} — V_{CE}



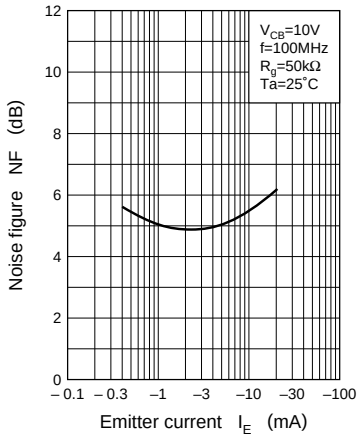
Z_{rb} — I_E



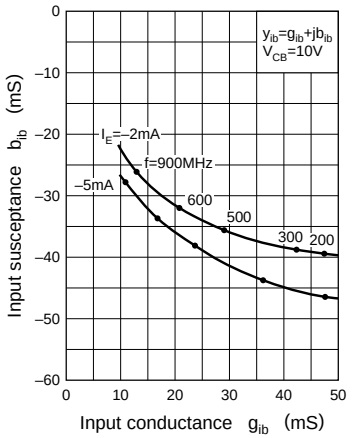
PG — I_E



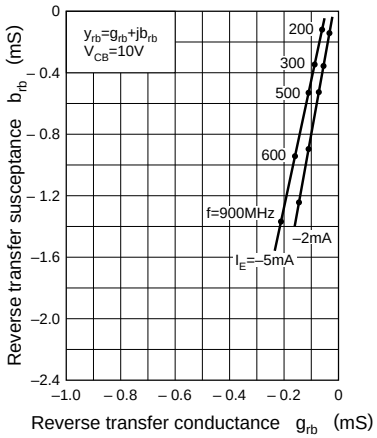
NF — I_E



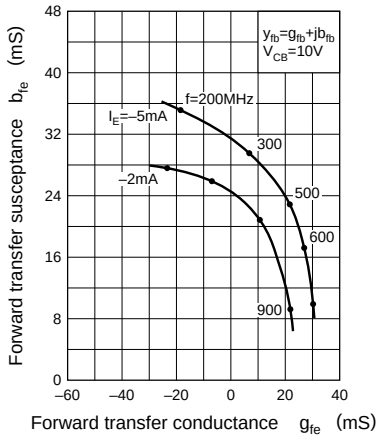
b_{ib} — g_{ib}



b_{rb} — g_{rb}



b_{fb} — g_{fb}



b_{ob} — g_{ob}